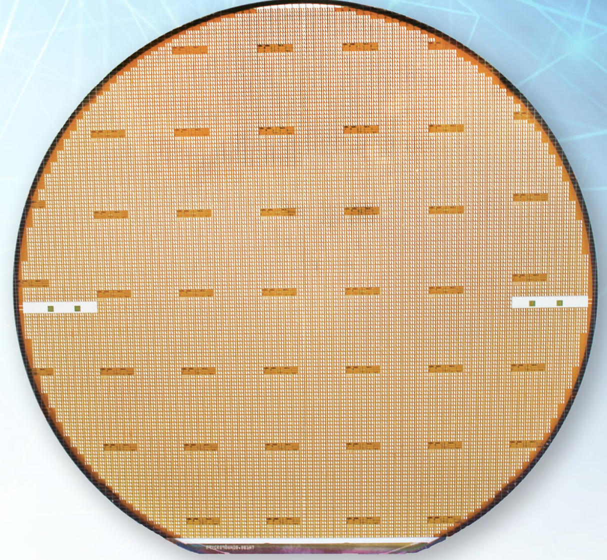
EPC
EFFICIENT POWER CONVERSION

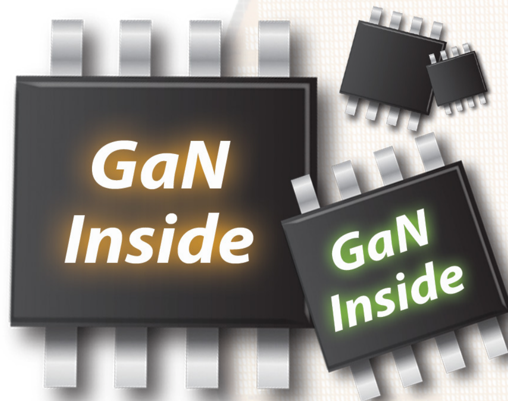
EPC Wafer Sales

EPC is pleased to offer our development partners the option of procuring EPC enhancement-mode gallium nitride (GaN) devices in wafer form for ease of integration. A variety of additional available services is detailed below. If you have specific requirements not addressed below, please contact us at **info@epc-co.com**



Wafer Sales and Services

- Bumped wafers
- Wafers without solder bumps
  - Under Bump Metal (UBM): 10 µm PI + 2 Ka Ti sputter + 4 Ka Cu sputter + 8 µm Cu plating
  - Under Bump Metal (UBM): 10 µm PI + 2 Ka Ti sputter + 4 Ka Cu sputter + 5 µm Cu/3 µm Ni plating
- Extra services available per wafer
  - Wafer thinning down to 260 µm
  - Metallization of the wafer backside
    - Ti/Ni/Au
    - Ti/Ni/Ag
  - Backside coating tape



For information on pricing and availability please contact your local sales representative or EPC @ info@epc-co.com

eGaN® FETs and ICs…

Faster, More Efficient, Smaller

EPC2040: 15 V, 28 A

EPC2035: 60 V, 24 A
EPC2203: 80 V, 17 A – **AEC-Q101 Qualified**
EPC2036: 100 V, 18 A
EPC2037: 100 V 2.4 A
EPC2038: 100 V with Gate Diode, 0.5 A

EPC2051: 100 V, 37 A

EPC2039: 80 V, 50 A

EPC2108: 60 V Dual with Sync Boot, 5.5 A / 0.5 A
EPC2107: 100 V Dual with Sync Boot, 3.8 A / 0.5 A
EPC2106: 100 V Half Bridge, 18 A
EPC2110: 120 V Dual Common Source, 20 A

EPC2052: 100 V, 70 A

EPC2012C: 200 V, 22 A

EPC2014C: 40 V , 60 A
EPC2007C: 100 V, 40 A

EPC2050: 350 V, 26 A

EPC8004: 40 V, 7.5 A
EPC8002: 65 V, 2 A
EPC8009: 65 V , 7.5 A
EPC8010: 100 V, 7.5 A

EPC2202: 80 V, 75 A – **AEC-Q101 Qualified**
EPC2212: 100 V, 75 A – **AEC-Q101 Qualified**
EPC2016C: 100 V, 75 A

EPC2049: 40 V, 175 A
EPC2045: 100 V, 130 A

EPC2019: 200 V, 42 A

EPC2053: 100 V, 240 A

EPC2010C: 200 V, 90 A

EPC2015C: 40 V, 235 A
EPC2001C: 100 V, 150 A